

NX3020NAKT

30 V, 180 mA N-channel Trench MOSFET

29 October 2013

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT416 (SC-75) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage

3. Applications

- · Relay driver
- · High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	180	mA
Static characte	Static characteristics						,
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$		-	2.7	4.5	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².





30 V, 180 mA N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 SC-75 (SOT416)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package	ge					
	Name	Description	Version				
NX3020NAKT	SC-75	plastic surface-mounted package; 3 leads	SOT416				

7. Marking

Table 4. Marking codes

Type number	Marking code
NX3020NAKT	VB

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	180	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	110	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	720	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[2]</u>	-	230	mW
			[1]	-	285	mW
		T _{sp} = 25 °C		-	1060	mW
Tj	junction temperature			-55	150	°C

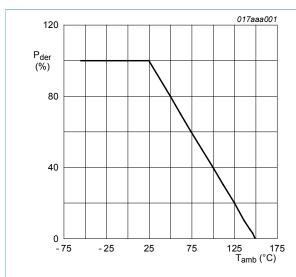
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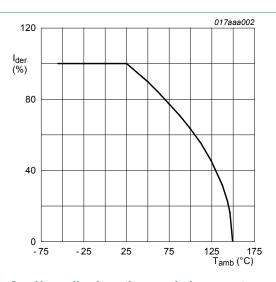
Symbol	Parameter	Conditions		Min	Max	Unit
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
Is	source current	T _{amb} = 25 °C	[1]	-	180	mA

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm². Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



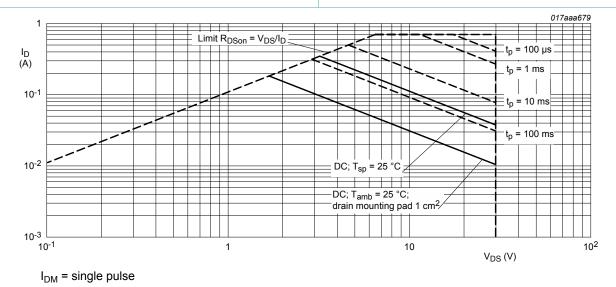
Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25\%)}} \times 100\%$$



Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-Fig. 3. source voltage

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Thermal characteristics

Table 6. **Thermal characteristics**

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	460	530	K/W
	from junction to ambient		[2]	-	370	430	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	115	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

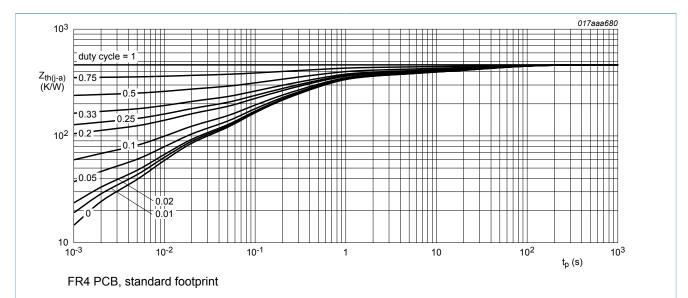
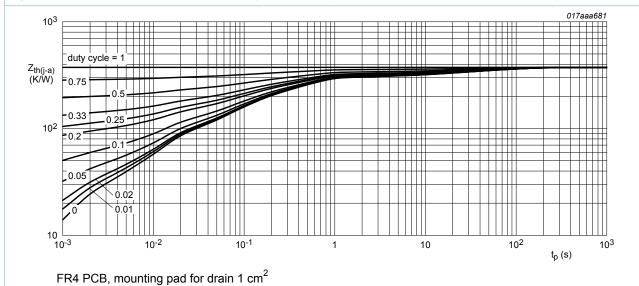


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 5.

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30 V, 180 mA N-channel Trench MOSFET

10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		,			
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \degree C$	0.8	1.2	1.5	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	3.5	μA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	3.5	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μΑ
	V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μA	
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.5	μA
R _{DSon} drain-source on-state		V_{GS} = 10 V; I_D = 100 mA; T_j = 25 °C	-	2.7	4.5	Ω
	resistance	V _{GS} = 10 V; I _D = 100 mA; T _j = 150 °C	-	5.5	9.2	Ω
	V _{GS} = 4.5 V; I _D = 100 mA; T _j = 25 °C	-	3	5.2	Ω	
	V_{GS} = 2.5 V; I_D = 10 mA; T_j = 25 °C	-	4	13	Ω	
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 150 mA; T_{j} = 25 °C	-	320	-	S
Dynamic ch	naracteristics		1	'		
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 150 mA; V _{GS} = 4.5 V;	-	0.34	0.44	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.11	-	nC
Q_{GD}	gate-drain charge		-	0.06	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	13	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.6	-	pF
C _{rss}	reverse transfer capacitance		-	1.1	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R_{L} = 250 Ω ; V_{GS} = 10 V;	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 ^{\circ}C$	-	5	-	ns
t _{d(off)}	turn-off delay time		-	34	68	ns
t _f	fall time		-	17	-	ns
Source-drai	in diode		1	1		
V _{SD}	source-drain voltage	I_S = 115 mA; V_{GS} = 0 V; T_j = 25 °C	0.47	0.7	1.2	V
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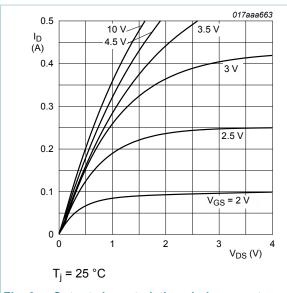


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

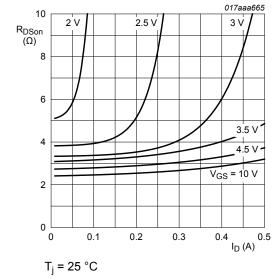


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

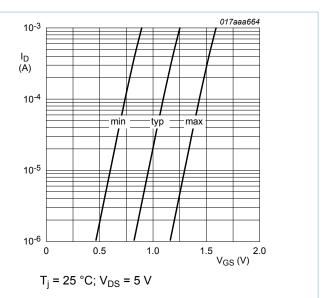


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

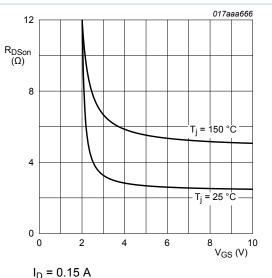


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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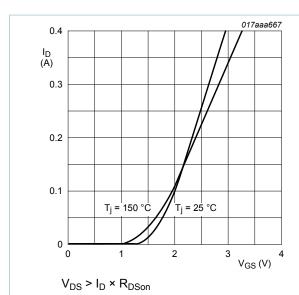


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

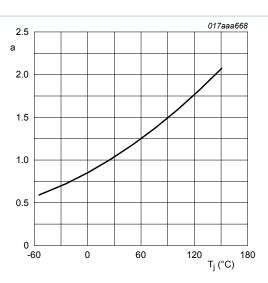


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

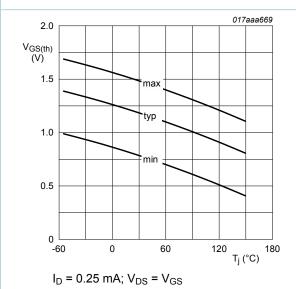


Fig. 12. Gate-source threshold voltage as a function of junction temperature

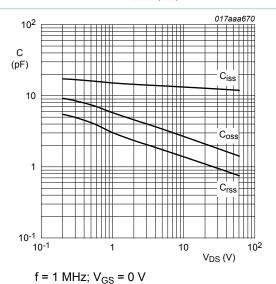


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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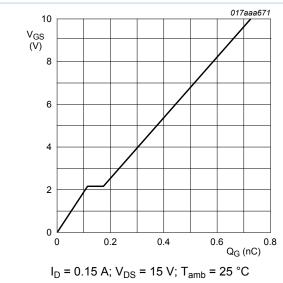


Fig. 14. Gate-source voltage as a function of gate charge; typical values

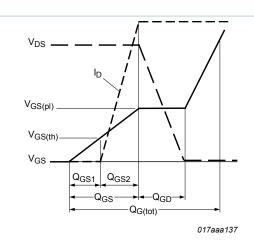


Fig. 15. Gate charge waveform definitions

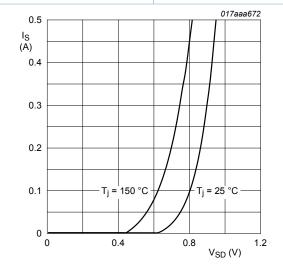
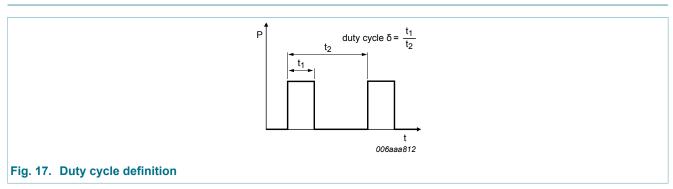


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$

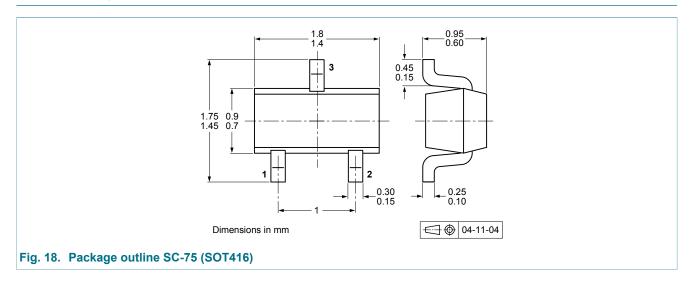


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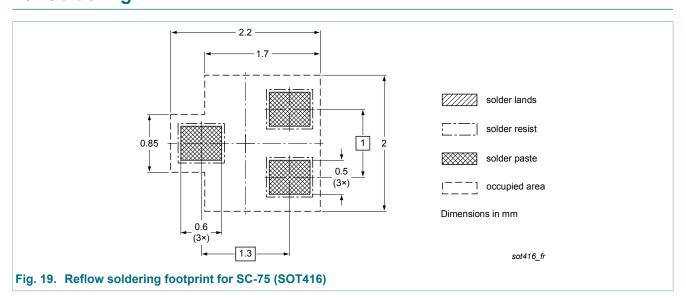
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30 V, 180 mA N-channel Trench MOSFET

12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
NX3020NAKT v.2	20131029	Product data sheet	-	NX3020NAKT v.1		
Modifications:	 Modifications: 3D package outline added Table 7 values of capacitance parameters corrected Figure 13 corrected 					
NX3020NAKT v.1	20120830	Product data sheet	-	-		

30 V, 180 mA N-channel Trench MOSFET

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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30 V, 180 mA N-channel Trench MOSFET

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Test information	8
12	Package outline	9
13	Soldering	9
14	Revision history	10
15	Legal information	11
15.1	Data sheet status	11
15.2	Definitions	11
15.3	Disclaimers	11
15.4	Trademarks	12

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13 / 13